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(under Article 11 of the Japanese Patent Law)

To the Examiner of the Patent Office Mr. Masaya ITO

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1. International Application No.

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4. Items to be amended

Claims

## 25 5. Contents of Amendments

(1) Claim 2 is amended as follows: "The display apparatus according to claim 1, wherein a source electrode of the thin film transistor is formed so as to be opposed to the pixel electrode in a thickness direction with the active

layer interposed therebetween." as originally filed is amended to "The display apparatus according to claim 1, wherein a source electrode of the thin film transistor is formed so as to be opposed to the pixel electrode in a thickness direction with the active layer interposed therebetween, and the pixel electrode has an area larger than that of the source electrode so as to cover the active layer on the source electrode substantially entirely."

6. List of attached documents

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(1) New sheet for page 11 (corresponding to pages 14 and 14/1 of the English translation) of the claims

## **CLAIMS**

[1] A display apparatus in which a pixel is driven by using a thin film transistor including an organic material in at least an active layer,

wherein the thin film transistor unit and a display element unit are laminated on a substrate in this order, and

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a pixel electrode formed on a substrate side of the display element unit also functions as a drain electrode of the thin film transistor.

[2] (Amended) The display apparatus according to claim 1, wherein a source electrode of the thin film transistor is formed so as to be opposed to the pixel electrode in a thickness direction with the active layer interposed therebetween, and

the pixel electrode has an area larger than that of the source electrode so as to cover the active layer on the source electrode substantially entirely.

- [3] The display apparatus according to claim 2, wherein the source electrode has an area not less than 25% the size of the pixel electrode.
- [4] The display apparatus according to any one of claims 1 to 3, wherein a conductive film for suppressing gas permeation of gas and moisture is formed outside of the display element unit.
- [5] The display apparatus according claim 4, wherein the conductive film is formed so as to cover an entire surface of a display region.
- [6] The display apparatus according any one of claims 1 to 5, wherein the substrate suppresses gas permeation of oxygen and moisture.
- 25 [7] The display apparatus according any one of claims 1 to 6, wherein the substrate is flexible.
  - [8] The display apparatus according any one of claims 1 to 7, wherein the display element unit is an organic electroluminescence element.

[9] The display apparatus according any one of claims 1 to 8, wherein the active layer unit of the thin film transistor includes an organic semiconductor layer.